TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOSVI-H)

# **TPCA8047-H**

Switching Regulator Applications Motor Drive Applications DC-DC Converter Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Qsw = 13 nC (typ.)
- Low drain-source ON-resistance:  $R_{DS}$  (ON) = 4.8  $m\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 92 S$  (typ.)
- Low leakage current:  $I_{DSS} = 10 \mu A (max) (V_{DS} = 40 V)$
- Enhancement mode:  $V_{th} = 1.3$  to 2.3 V ( $V_{DS} = 10$  V,  $I_D = 0.5$  mA)

### **Absolute Maximum Ratings (Ta = 25°C)**

Characte	eristic	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	40	V	
Drain-gate voltage (R	$k_{GS} = 20 \text{ k}\Omega$ )	$V_{DGR}$	40	V	
Gate-source voltage		$V_{GSS}$	±20	V	
Drain current	DC (Note 1)	ΙD	32	Α	
Drain current	Pulsed (Note 1)	$I_{DP}$	96	^	
Drain power dissipati	on (Tc = 25°C)	$P_{D}$	45	W	
Drain power dissipati	on (t = 10 s) (Note 2a)	P <sub>D</sub>	2.8	W	
Drain power dissipati	on (t = 10 s) (Note 2b)	P <sub>D</sub>	1.6	W	
Single-pulse avalance	ne energy (Note 3)	E <sub>AS</sub>	95	mJ	
Avalanche current		I <sub>AR</sub>	32	Α	
Repetitive avalanche	energy c = 25°C) (Note 4)	E <sub>AR</sub>	3.95	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature	range	T <sub>stg</sub>	-55 to 150	°C	

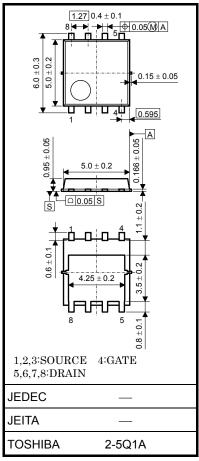
Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the

reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

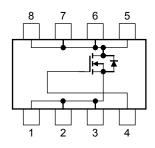
This transistor is an electrostatic-sensitive device. Handle with care.

#### Unit: mm



Weight: 0.069 g (typ.)

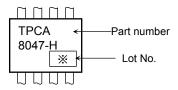
#### **Circuit Configuration**



### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25°C)	R <sub>th (ch-c)</sub>	2.78	°C/W
Thermal resistance, channel to ambient $(t=10\;s) \eqno(Note\;2a)$	R <sub>th (ch-a)</sub>	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	78.1	°C/W

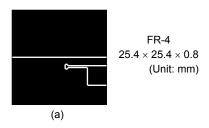
### Marking (Note 5)

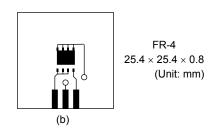


Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)

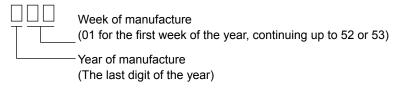




Note 3:  $V_{DD}$  = 24 V,  $T_{ch}$  = 25°C (initial), L = 100  $\mu$ H,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 32 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)



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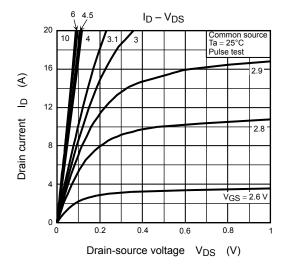
## **Electrical Characteristics (Ta = 25°C)**

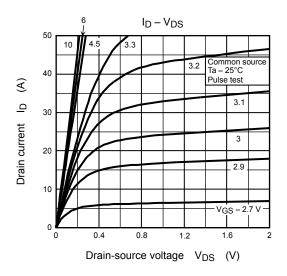
Ch	Characteristic Symbol		Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cutoff curre	ent	I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V	_	_	10	μА
Drain source bro	akdown voltago	V <sub>(BR)</sub> DSS	$I_D = 10$ mA, $V_{GS} = 0$ V	40	_	_	V
Dialii-source brea	akuowii voitage	V <sub>(BR) DSX</sub>	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	25	_	_	V
Gate threshold vo	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, I_D = 0.5 \text{ mA}$	1.3	_	2.3	>
Drain-source ON	rain-source ON-resistance		$V_{GS} = 4.5 \text{ V}, I_D = 16 \text{ A}$		6.0	8.5	mΩ
Dialii-source ON	-iesistance	NDS (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 16 A	_	- ±100 - 10 2.3	1115.2	
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 16 A	46	92	_	S
Input capacitance	9	C <sub>iss</sub>			2590	3365	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	135	200	pF
Output capacitance		C <sub>oss</sub>		_	440	_	
Gate resistance		rg	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	1.0	1.5	Ω
Gate resistance	Rise time	t <sub>r</sub>	10 V 🗍 In = 16 A	_	4.8	_	
Switching time	V (BR) DSS   ID = 10 mA, VGS = 0 V   40		ne				
Switching time	Fall time	t <sub>f</sub>	R = 1.7 Ω		9.9	8.5  7.3   0 3365  5 200  0  1.5	ns
	Turn-off time	t <sub>off</sub>		_	43	_	
Total gate charge	)	0	$V_{DD} \approx 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 32 \text{ A}$	_	43	3 —	
(gate-source plus	s gate-drain)	Уg	$V_{DD} \approx 32 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 32 \text{ A}$		23	_	
Gate-source charge 1		Q <sub>gs1</sub>		_	7.9	_	nC
Gate-drain ("Miller") charge		Q <sub>gd</sub>	$V_{DD} \approx 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 32 \text{ A}$	_	8.4	_	
Gate switch char	ge	Q <sub>SW</sub>		_	13	_	

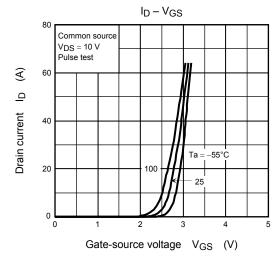
### **Source-Drain Ratings and Characteristics (Ta = 25°C)**

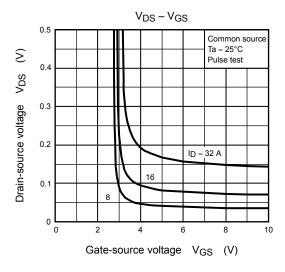
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Drain reverse current	Pulse	(Note 1)	I <sub>DRP</sub>	_	_	_	96	Α
Forward voltage (diode)			$V_{DSF}$	$I_{DR} = 32 \text{ A}, V_{GS} = 0 \text{ V}$	_		-1.2	V

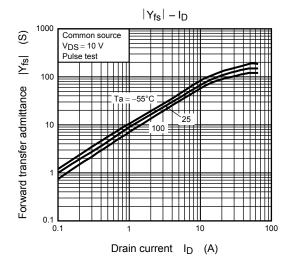
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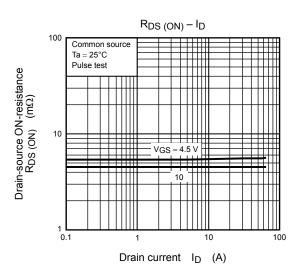




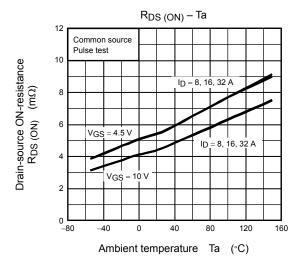


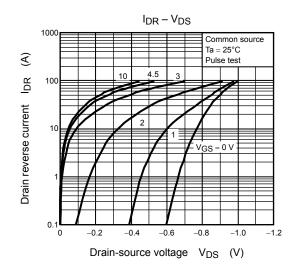


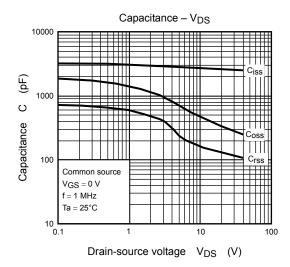


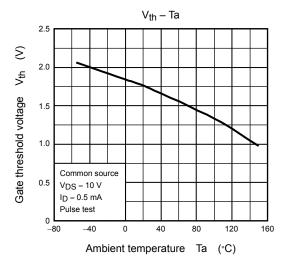


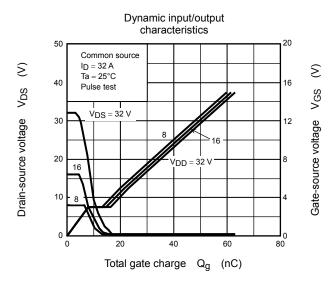
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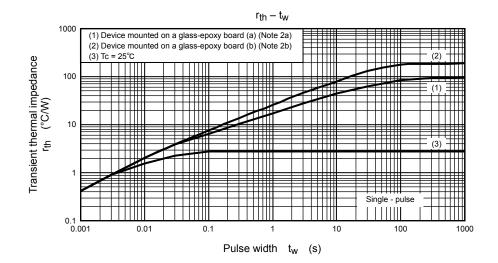


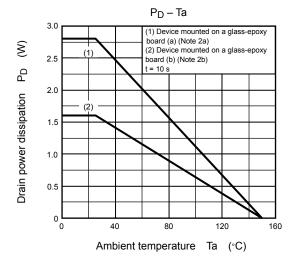


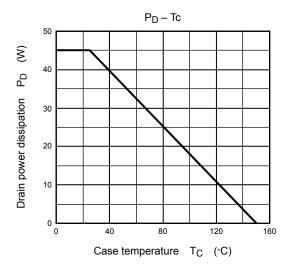


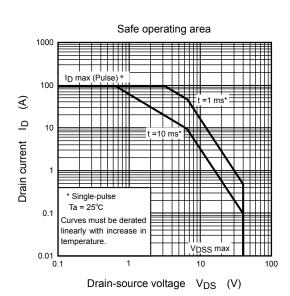


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